

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-30V	15.5mΩ@-10V	-9.1A
	20mΩ@-4.5V	

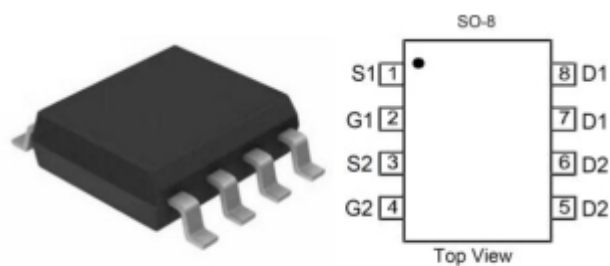
## Feature

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed

## Application

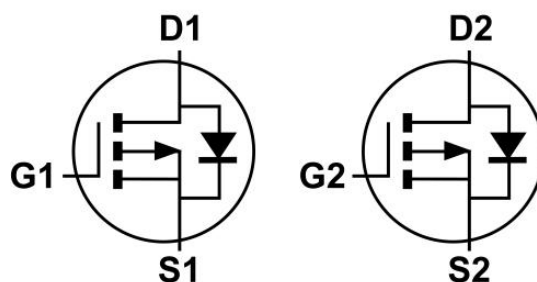
- DC-DC Converters
- Power Management Functions
- Backlighting

## Package

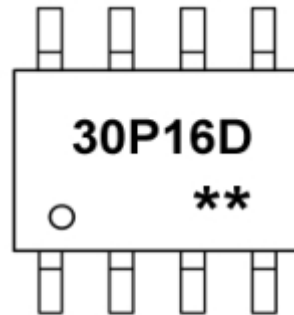


**SOP-8**

## Circuit diagram



## Marking



**30P16D =Device Code**  
**\*\* =Week Code**

## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	-9.1	A
Pulsed Drain Current <sup>1)</sup>	I <sub>DM</sub>	-36	A
Power Dissipation	P <sub>D</sub>	1.5	W
Thermal Resistance from Junction to Ambient <sup>2)</sup>	R <sub>θJA</sub>	85	°C
Junction Temperature	T <sub>J</sub>	150	
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

## Electrical characteristics

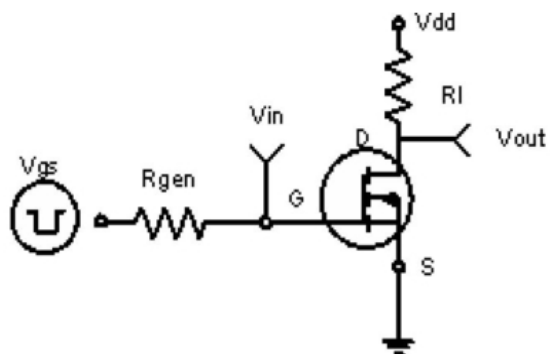
( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V			-1	uA
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	uA
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.5	-3	V
Drain-Source On-Resistance <sup>1</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -9.1A		15.5	20	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -6.9A		20	35	
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz		1600		pF
Output Capacitance	C <sub>oss</sub>			350		
Reverse Transfer Capacitance	C <sub>rss</sub>			300		
Switching Characteristics						
Turn-on Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> = -15V, I <sub>D</sub> = -1A , V <sub>GS</sub> = -10V, R <sub>GEN</sub> = 6Ω		10		nS
Turn-on Rise Time	T <sub>r</sub>			15		
Turn-off Delay Time	T <sub>d(off)</sub>			110		
Turn-off Fall Time	T <sub>f</sub>			70		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -9.1V, I <sub>D</sub> = -10A		30		nC
Gate-Source Charge	Q <sub>gs</sub>			5.5		
Gate-Drain Charge	Q <sub>gd</sub>			8		
Drain-Source Diode Characteristics						
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V			-1.2	V

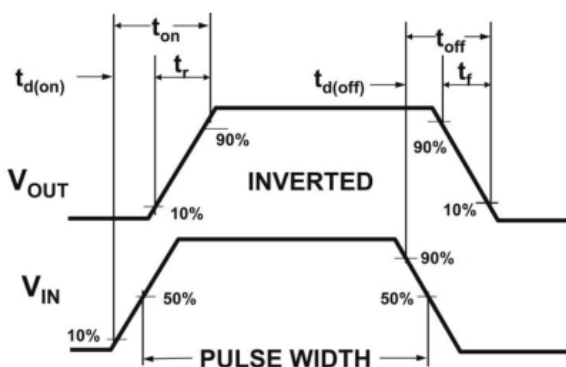
### Note:

1. Repetitive rating: Pulse width limited by junction temperature.
2. Surface mounted on FR4 board,  $t \leq 10s$ .

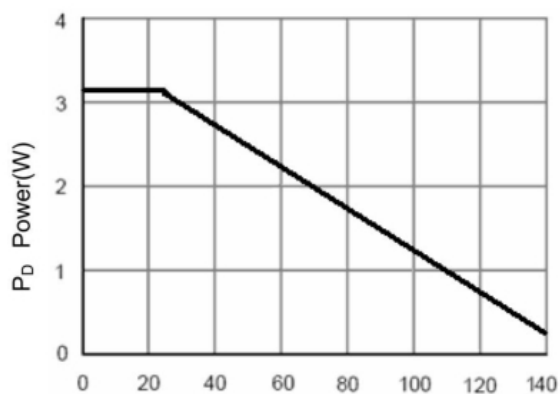
## Typical Characteristics



Switching Test Circuit

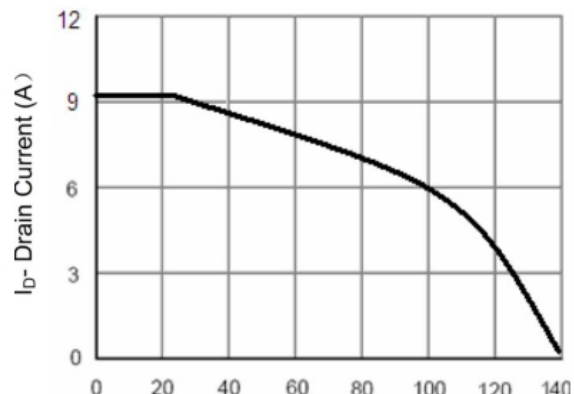


Switching Waveforms



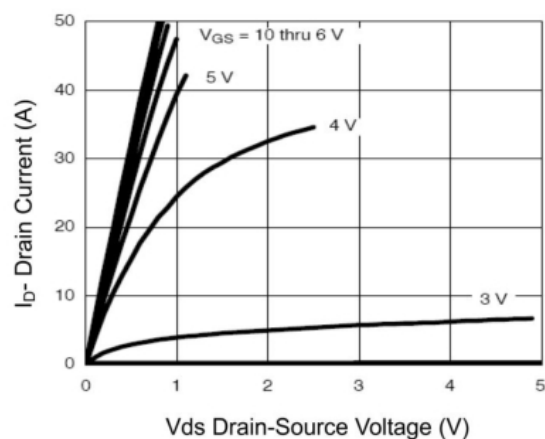
$T_J$ -Junction Temperature(°C)

Power Dissipation



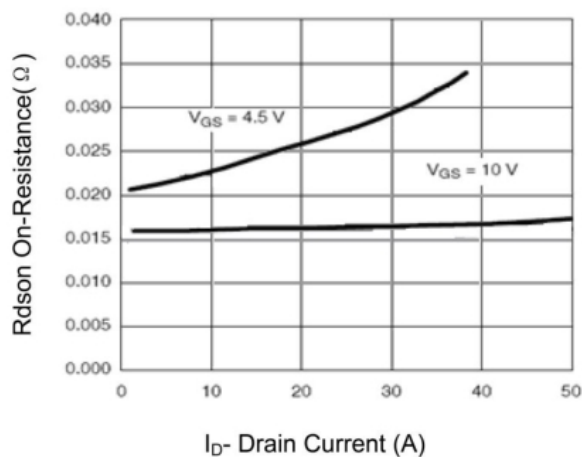
$T_J$ -Junction Temperature(°C)

Drain Current



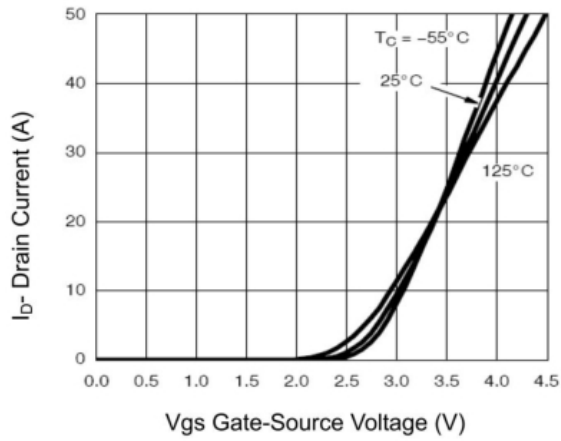
$V_{GS} = 10 \text{ thru } 6 \text{ V}$

Output Characteristics

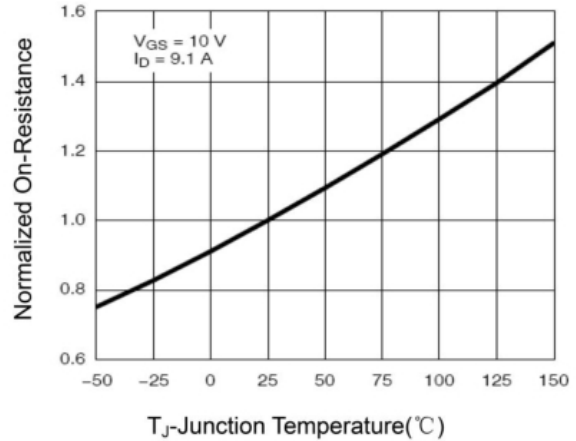


$I_D$ - Drain Current (A)

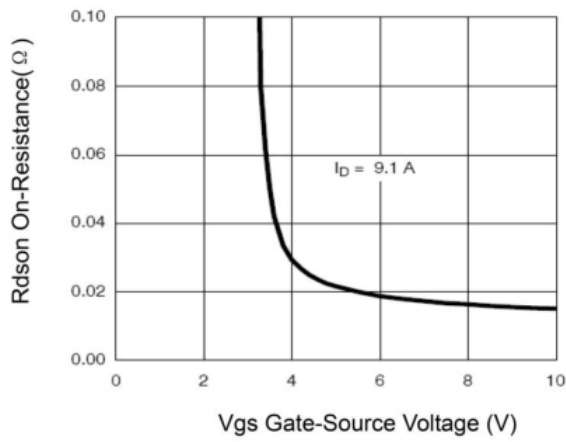
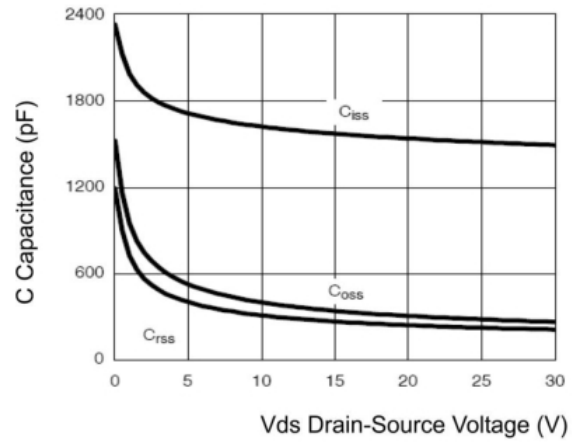
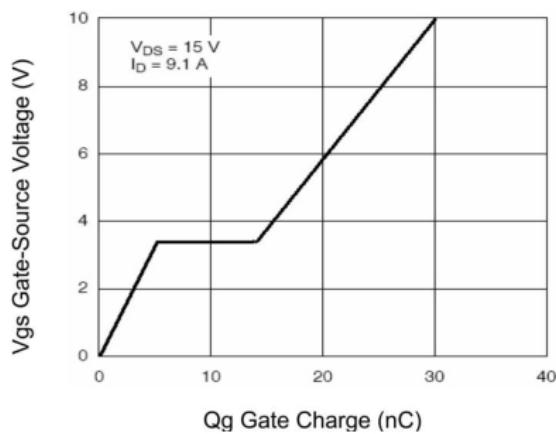
Drain-Source On-Resistance



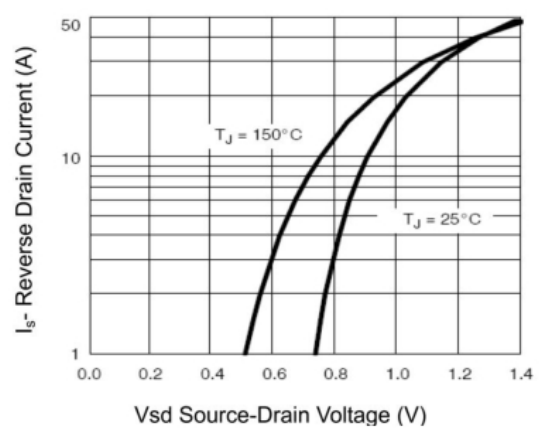
Transfer Characteristics



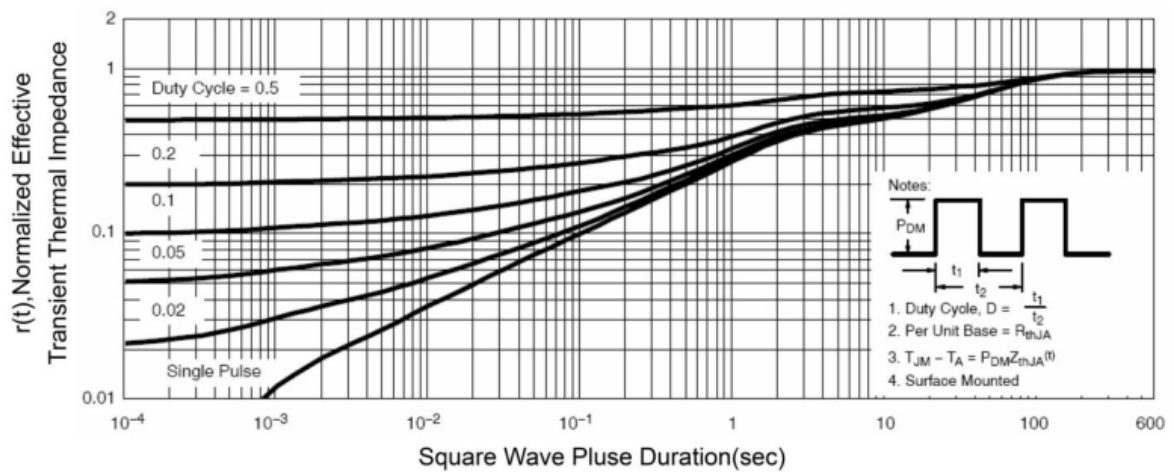
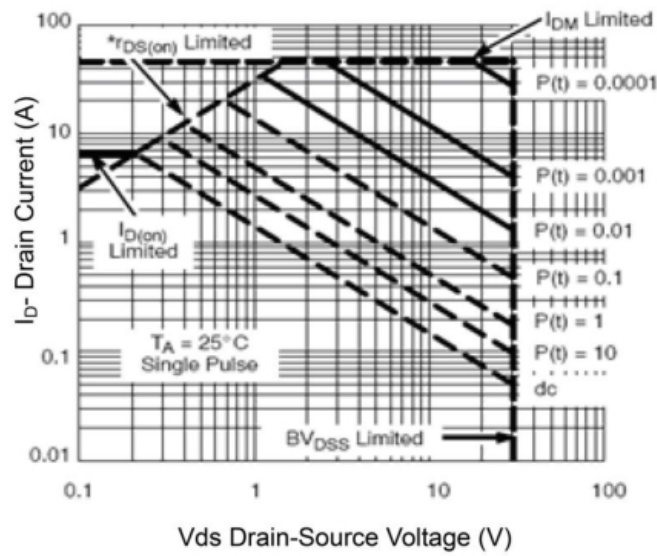
Drain-Source On-Resistance


 $R_{DS(on)}$  vs  $V_{GS}$ 

Capacitance vs  $V_{DS}$ 


Gate Charge

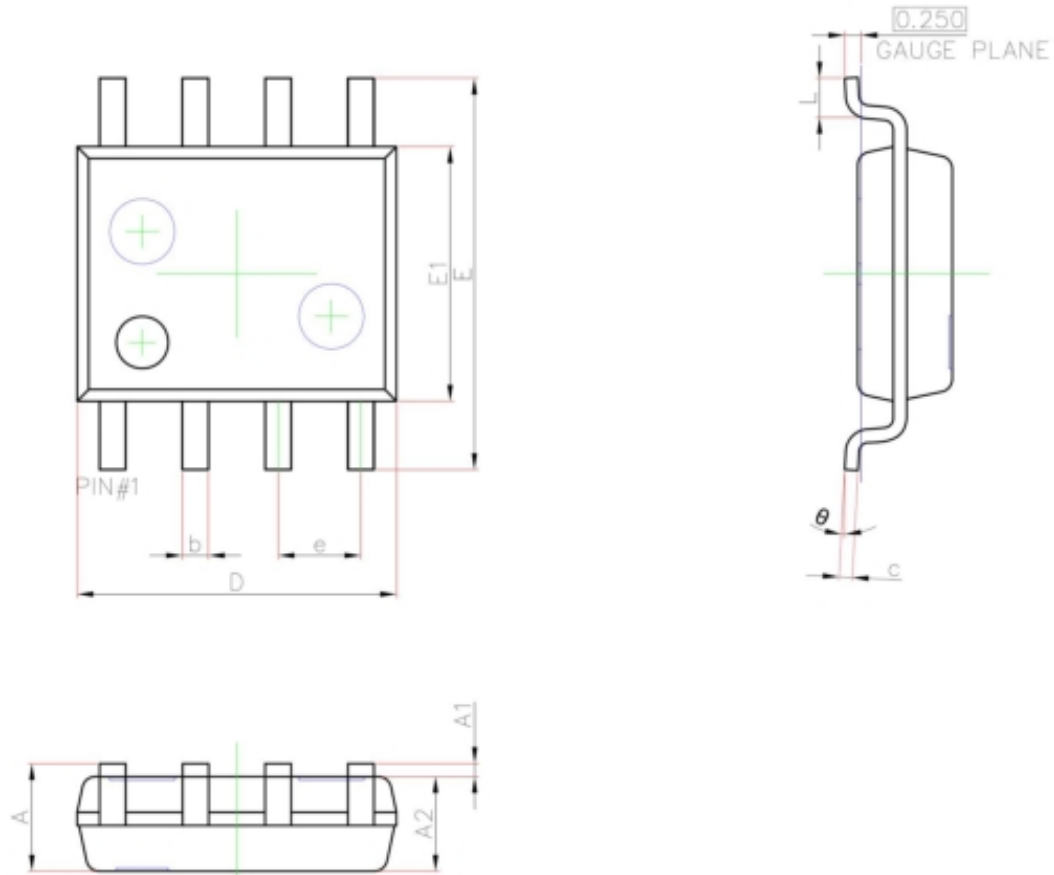


Source- Drain Diode Forward



**Normalized Maximum Transient Thermal Impedance**

## SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.450	1.750	0.057	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
$\theta$	0°	8°	0°	8°